### **INTEGRATED CIRCUITS**

# DATA SHEET

For a complete data sheet, please also download:

- The IC04 LOCMOS HE4000B Logic Family Specifications HEF, HEC
- The IC04 LOCMOS HE4000B Logic Package Outlines/Information HEF, HEC

# HEF4093B gates Quadruple 2-input NAND Schmitt trigger

Product specification
File under Integrated Circuits, IC04

January 1995



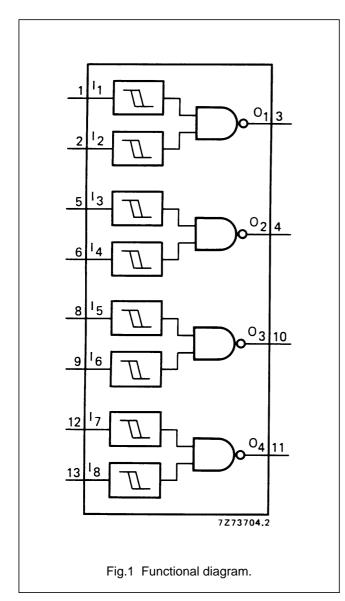


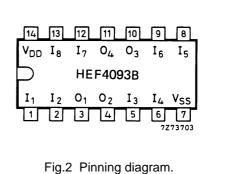
### **Quadruple 2-input NAND Schmitt trigger**

HEF4093B gates

#### **DESCRIPTION**

The HEF4093B consists of four Schmitt-trigger circuits. Each circuit functions as a two-input NAND gate with Schmitt-trigger action on both inputs. The gate switches at different points for positive and negative-going signals. The difference between the positive voltage ( $V_P$ ) and the negative voltage ( $V_N$ ) is defined as hysteresis voltage ( $V_H$ ).





HEF4093BP(N): 14-lead DIL; plastic

(SOT27-1)

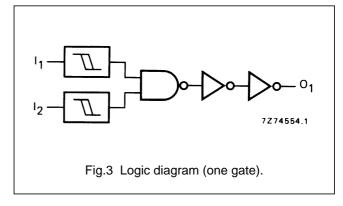
HEF4093BD(F): 14-lead DIL; ceramic (cerdip)

(SOT73)

HEF4093BT(D): 14-lead SO; plastic

(SOT108-1)

(): Package Designator North America



FAMILY DATA, I<sub>DD</sub> LIMITS category GATES

See Family Specifications

Philips Semiconductors Product specification

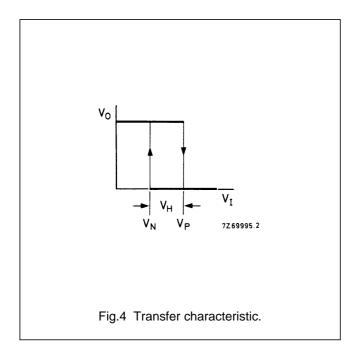
# Quadruple 2-input NAND Schmitt trigger

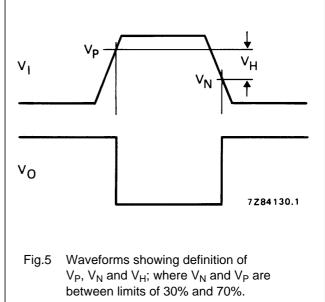
HEF4093B gates

#### **DC CHARACTERISTICS**

 $V_{SS}$  = 0 V;  $T_{amb}$  = 25 °C

	V <sub>DD</sub> V	SYMBOL	MIN.	TYP.	MAX.	
Hysteresis	5		0,4	0,7	_	V
voltage	10	V <sub>H</sub>	0,6	1,0	_	V
	15		0,7	1,3	_	V
Switching levels	5		1,9	2,9	3,5	V
positive-going	10	V <sub>P</sub>	3,6	5,2	7	V
input voltage	15		4,7	7,3	11	V
negative-going	5		1,5	2,2	3,1	V
input voltage	10	V <sub>N</sub>	3	4,2	6,4	V
	15		4	6,0	10,3	V





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# Quadruple 2-input NAND Schmitt trigger

HEF4093B gates

#### **AC CHARACTERISTICS**

 $V_{SS}$  = 0 V;  $T_{amb}$  = 25 °C;  $C_L$  = 50 pF; input transition times  $\leq$  20 ns

	V <sub>DD</sub>	SYMBOL	TYP.	MAX.	TYPICAL EXTRAPOLATION FORMULA
Propagation delays	5		90	185 ns	63 ns + (0,55 ns/pF) C <sub>L</sub>
$I_n \rightarrow O_n$	10	t <sub>PHL</sub>	40	80 ns	29 ns + (0,23 ns/pF) C <sub>L</sub>
HIGH to LOW	15		30	60 ns	22 ns + (0,16 ns/pF) C <sub>L</sub>
	5		85	170 ns	58 ns + (0,55 ns/pF) C <sub>L</sub>
LOW to HIGH	10	t <sub>PLH</sub>	40	80 ns	29 ns + (0,23 ns/pF) C <sub>L</sub>
	15		30	60 ns	22 ns + (0,16 ns/pF) C <sub>L</sub>
Output transition times	5		60	120 ns	10 ns + (1,0 ns/pF) C <sub>L</sub>
HIGH to LOW	10	t <sub>THL</sub>	30	60 ns	9 ns + (0,42 ns/pF) C <sub>L</sub>
	15		20	40 ns	6 ns + (0,28 ns/pF) C <sub>L</sub>
	5		60	120 ns	10 ns + (1,0 ns/pF) C <sub>L</sub>
LOW to HIGH	10	t <sub>TLH</sub>	30	60 ns	9 ns + (0,42 ns/pF) C <sub>L</sub>
	15		20	40 ns	6 ns + (0,28 ns/pF) C <sub>L</sub>

	V <sub>DD</sub> V	TYPICAL FORMULA FOR P (μW)	
Dynamic power	5	$1300 f_i + \sum (f_o C_L) \times V_{DD}^2$	where
dissipation per	10	$6400 f_i + \sum (f_o C_L) \times V_{DD}^2$	f <sub>i</sub> = input freq. (MHz)
package (P)	15	18 700 $f_i + \sum (f_o C_L) \times V_{DD}^2$	f <sub>o</sub> = output freq. (MHz)
			C <sub>L</sub> = load capacitance (pF)
			$\sum (f_o C_L) = \text{sum of outputs}$
			V <sub>DD</sub> = supply voltage (V)

### Quadruple 2-input NAND Schmitt trigger

HEF4093B gates

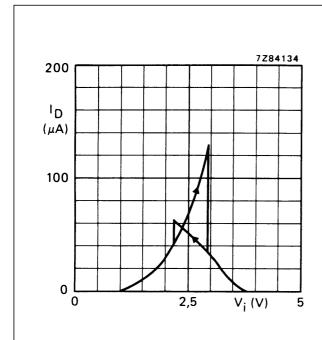


Fig.6 Typical drain current as a function of input voltage;  $V_{DD} = 5 \text{ V}$ ;  $T_{amb} = 25 \text{ °C}$ .

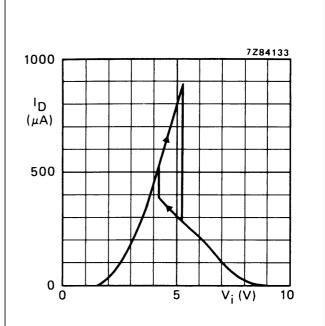


Fig.7 Typical drain current as a function of input voltage;  $V_{DD}$  =10 V;  $T_{amb}$  = 25 °C.

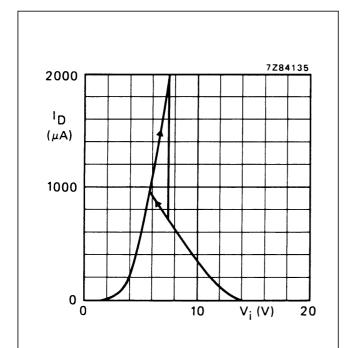
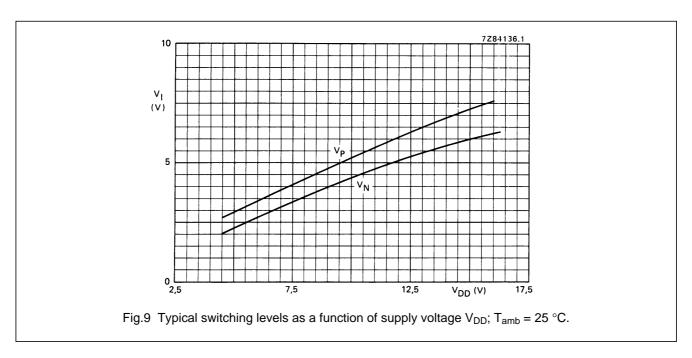


Fig.8 Typical drain current as a function of input voltage;  $V_{DD} = 15 \text{ V}$ ;  $T_{amb} = 25 ^{\circ}\text{C}$ .

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## Quadruple 2-input NAND Schmitt trigger

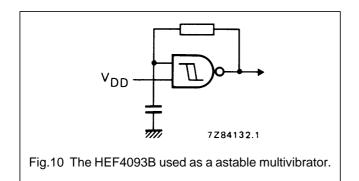
HEF4093B gates

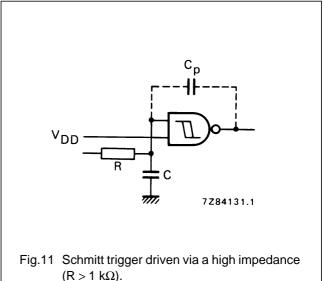


#### **APPLICATION INFORMATION**

Some examples of applications for the HEF4093B are:

- Wave and pulse shapers
- · Astable multivibrators
- · Monostable multivibrators.





If a Schmitt trigger is driven via a high impedance (R > 1  $k\Omega$ ) then it is necessary to incorporate a capacitor C of such value that:

 $\frac{C}{C_D} > \frac{V_{DD} - V_{SS}}{V_H}$ , otherwise oscillation can occur on the edges of a pulse.

 $C_p$  is the external parasitic capacitance between inputs and output; the value depends on the circuit board layout.

#### Note

The two inputs may be connected together, but this will result in a larger through-current at the moment of switching.